

FCP11N60 / FCPF11N60 / FCPF11N60T

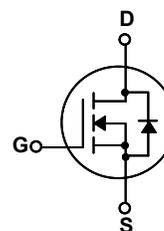
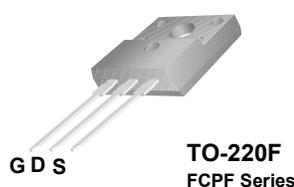
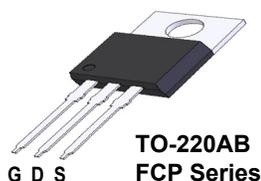
General Description

SuperFET™ is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.

Features

- 650V @ T_j = 150°C
- Typ. R_{ds(on)} = 0.32Ω
- Ultra low gate charge (typ. Q_g=40nC)
- Low effective output capacitance (typ. C_{oss,eff} = 95pF)
- 100% avalanche tested
- RoHS Compliant



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FCP11N60	FCPF11N60(T)	Units
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	11	11*	A
		7	7*	A
I _{DM}	Drain Current - Pulsed (Note 1)	33	33*	A
V _{GSS}	Gate-Source Voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	340		mJ
I _{AR}	Avalanche Current (Note 1)	11		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	12.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	125	36	W
		1.0	0.29	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCP11N60	FCPF11N60(T)	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	1.0	3.5	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink	0.5	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Elerical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}, T_J = 25^\circ\text{C}$	600	--	--	V
		$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}, T_J = 150^\circ\text{C}$	--	650	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.6	--	V/ $^\circ\text{C}$
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 11\text{ A}$	--	700	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$	--	0.32	0.38	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 5.5\text{ A}$ (Note 4)	--	9.7	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1148	1490	pF
C_{oss}	Output Capacitance		--	671	870	pF
C_{rss}	Reverse Transfer Capacitance		--	63	82	pF
C_{oss}	Output Capacitance	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	35	--	pF
$C_{oss\text{ eff.}}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	--	95	--	pF
ESR	Equivalent Series Resistance	Drain Open, $f=1\text{MHz}$	--	2.5	--	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 11\text{ A},$ $R_G = 25\ \Omega$	--	34	80	ns
t_r	Turn-On Rise Time		--	98	205	ns
$t_{d(off)}$	Turn-Off Delay Time		--	119	250	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	56	120
Q_g	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}$	--	40	52	nC
Q_{gs}	Gate-Source Charge		--	7.2	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	21	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	11	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	33	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 11\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 11\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	390	--	ns
Q_{rr}	Reverse Recovery Charge	(Note 4)	--	5.7	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS} = 5.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 11\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

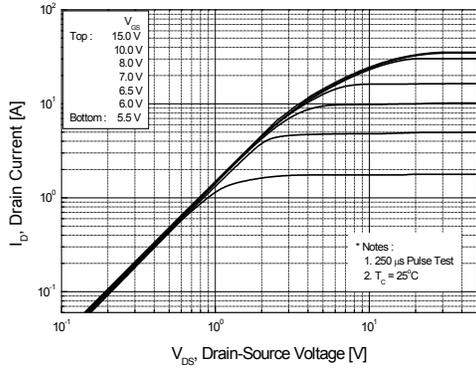


Figure 1. On-Region Characteristics

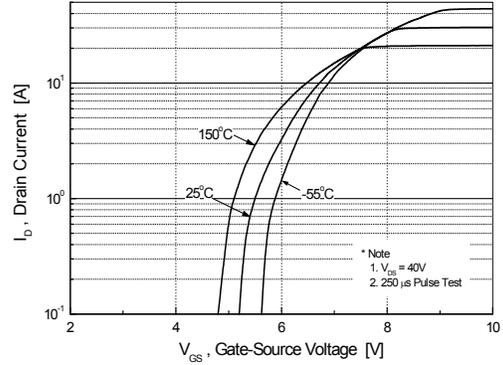


Figure 2. Transfer Characteristics

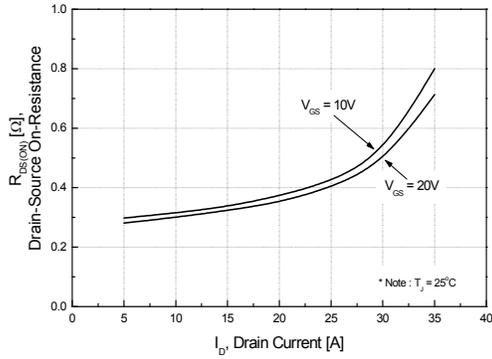


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

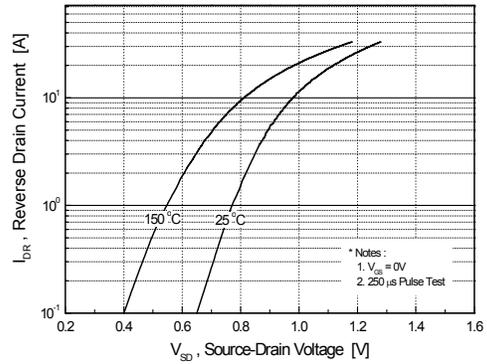


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

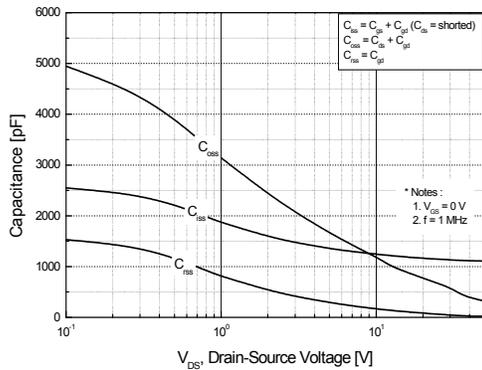


Figure 5. Capacitance Characteristics

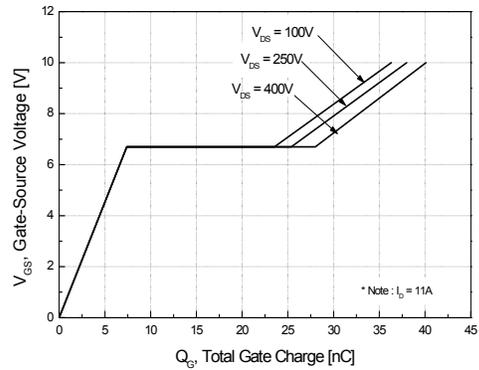


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

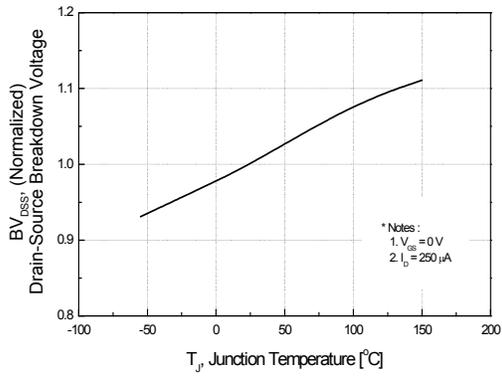


Figure 7. Breakdown Voltage Variation vs. Temperature

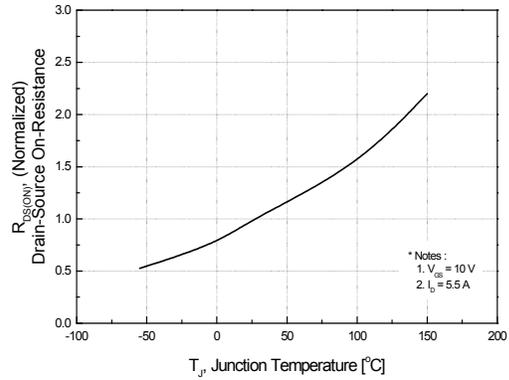


Figure 8. On-Resistance Variation vs. Temperature

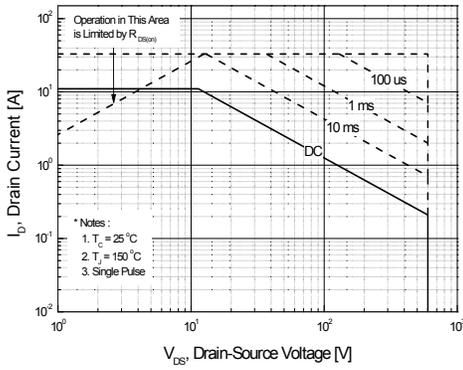


Figure 9-1. Maximum Safe Operating Area for FCP11N60

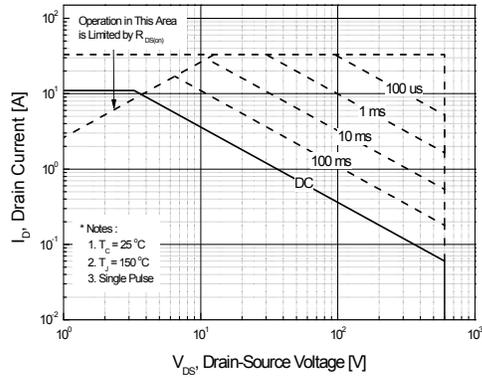


Figure 9-2. Maximum Safe Operating Area for FCPF11N60(T)

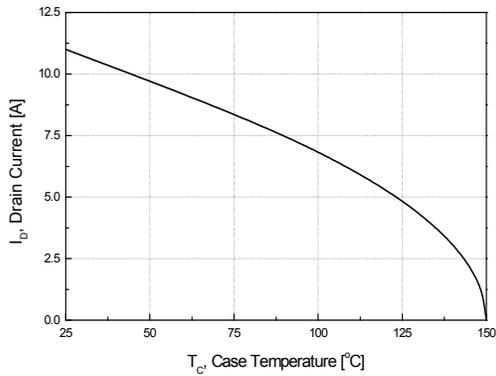


Figure 10. Maximum Drain Current vs. Case Temperature

Typical Characteristics (Continued)

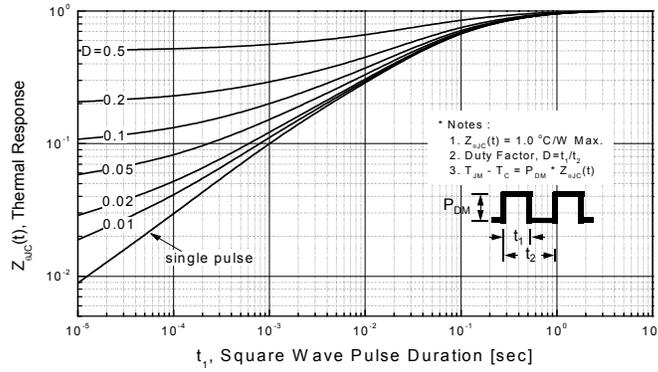


Figure 11-1. Transient Thermal Response Curve for FCP11N60

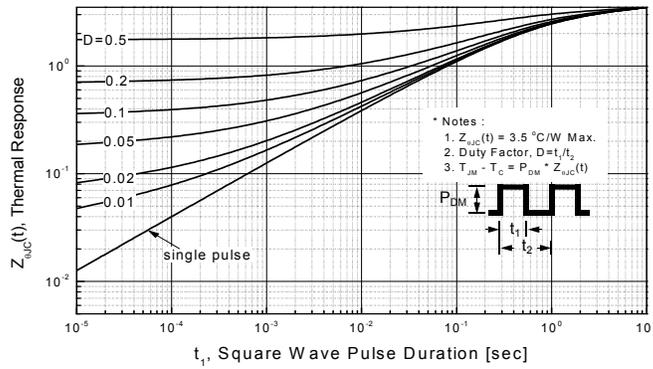
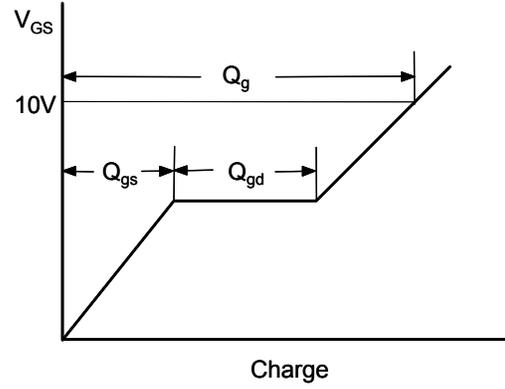
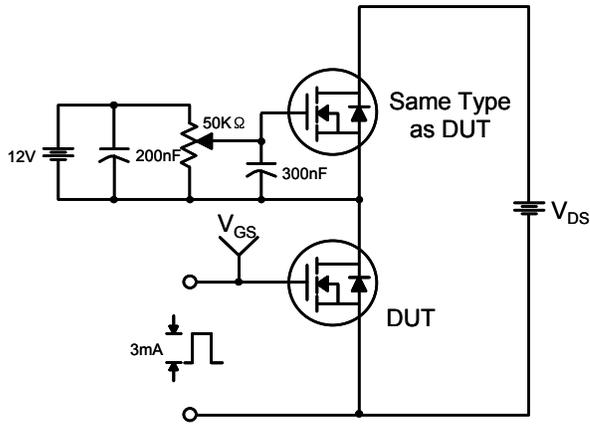
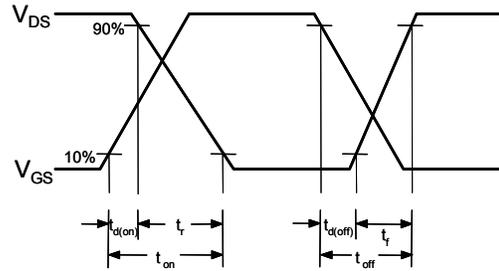
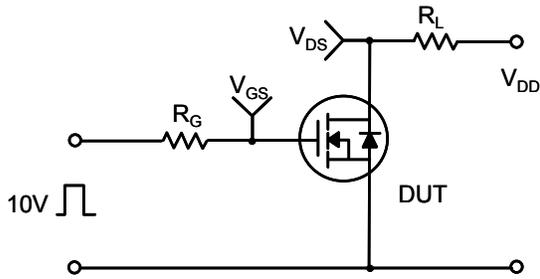


Figure 11-2. Transient Thermal Response Curve for FCPF11N60(T)

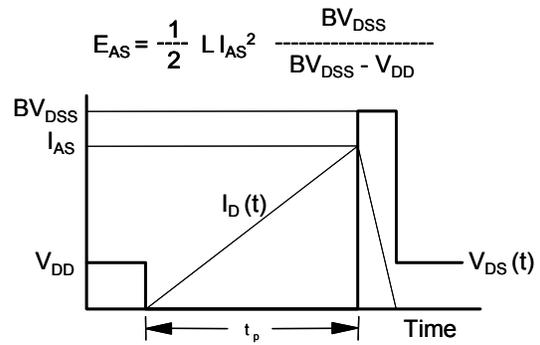
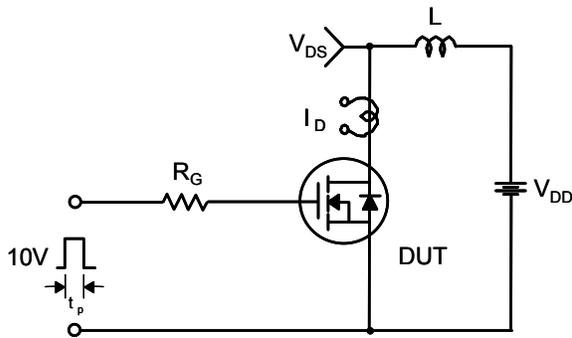
Gate Charge Test Circuit & Waveform



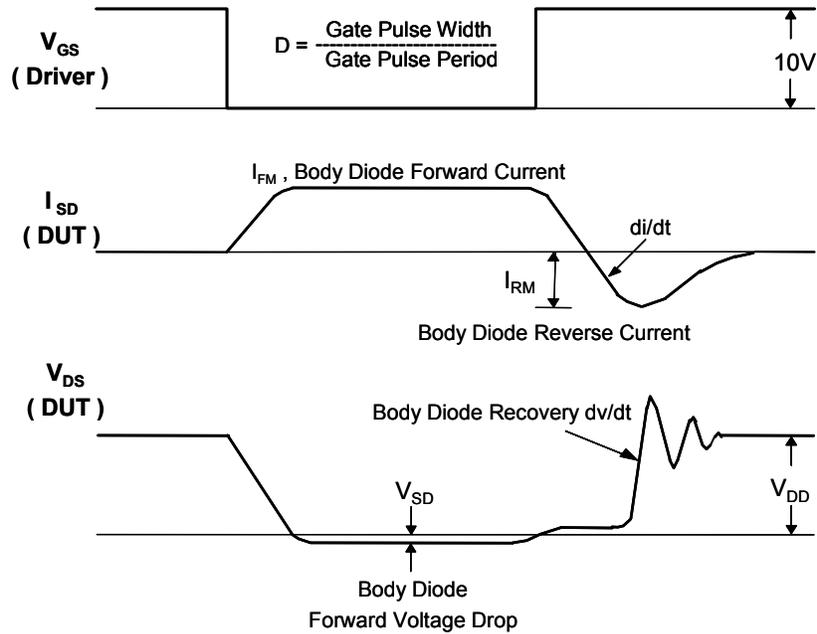
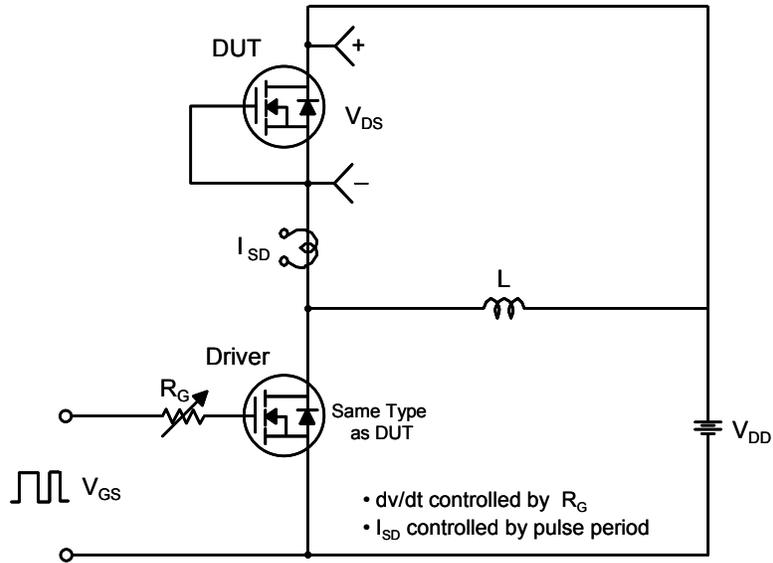
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

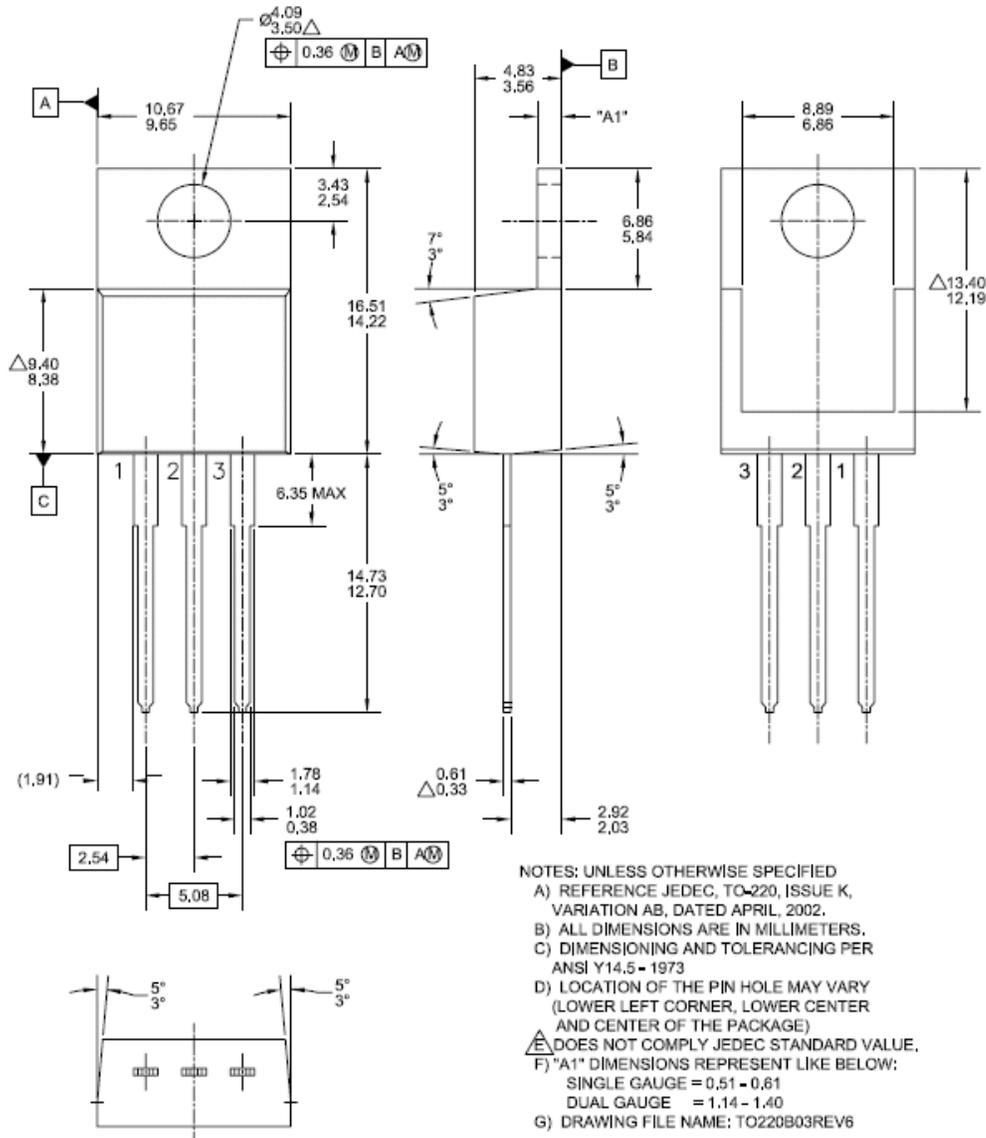


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-220AB

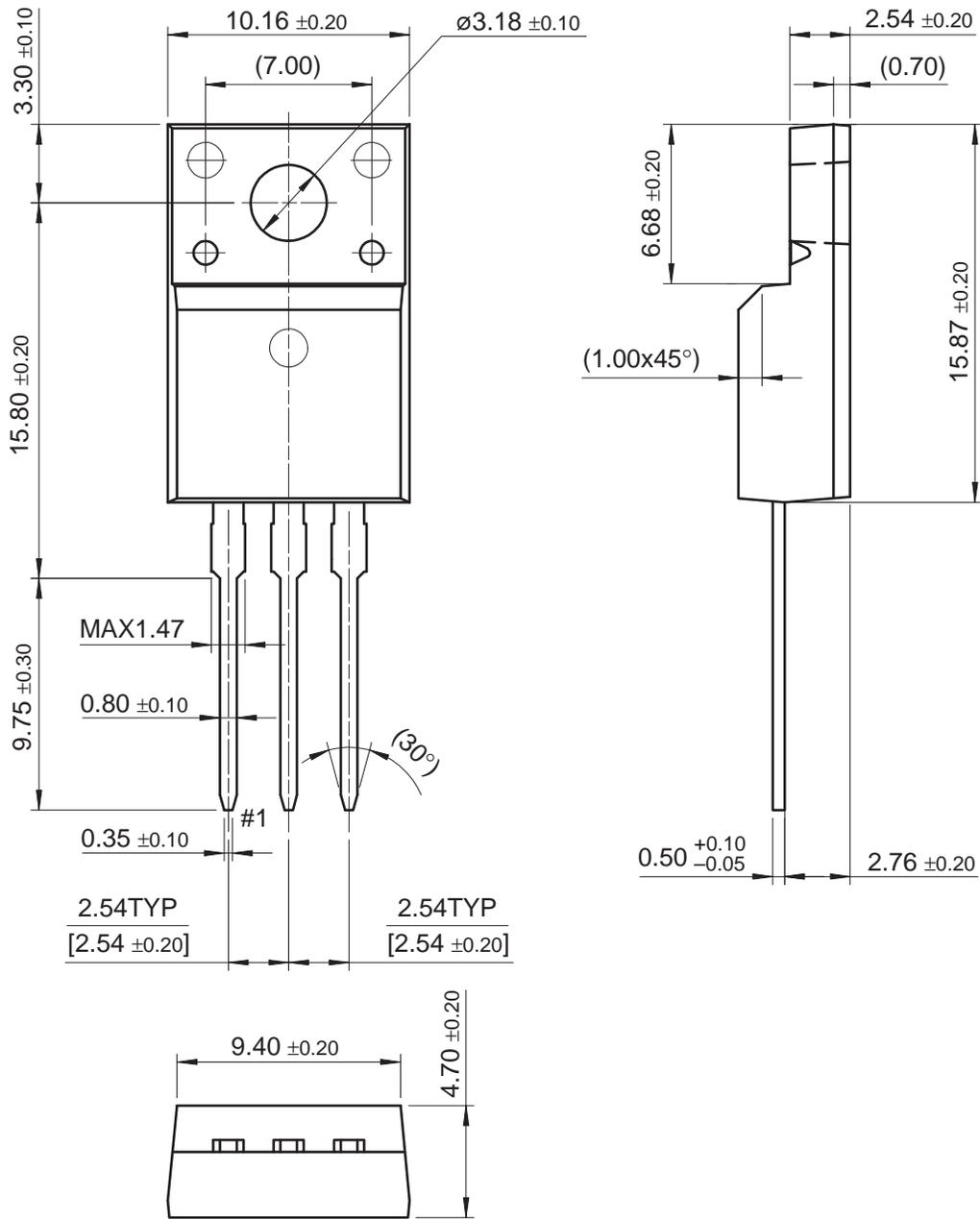


FCP11N60 / FCPF11N60 / FCPF11N60T

Dimensions in Millimeters

Mechanical Dimensions

TO-220F



FCP11N60 / FCP11N60T / FCP11N60

Dimensions in Millimeters



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